Supporting Information

Thickness Optimization of Zn0.9Mg0.1O Nanoparticle Electron Transport Layer for High-Performance Top-Emission Quantum Dot Light-Emitting Diodes

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Figure S1. Electroluminescence characteristics of QLEDs with a 50 nm-thick Zn0.9Mg0.1O NP ETLs inside the bank enclosure and without bank: (a) Current density curves as a function of voltage, (b) Luminance curves as a function of voltage, (c) current efficiency curves as a function of current density, and electroluminescence spectra of the QLEDs utilizing Zn0.9Mg0.1O NP ETLs